6509688102



| U.S. DEP                    | PTO-1449 (Modified)                                  |               | ATTY. DOCKET NO.   | SERIAL                           | NUM BER                    |                    |
|-----------------------------|--|---------------|--|----------------------------------|----------------------------|--------------------|
| U.S. DEP                    | •  |               |  |                                  |                            |                    |
|                             |  |               | 211.004-US   |                                  | 10/840,0                   | 09                 |
| PATENT AND TRADEMARK OFFICE |  |               | APPLICANT(S) Forrant et al.  |                                  |                            |                    |
| INPORMATI                   | ON DISCLOSURE S                                      | TATEMENT      | FILING DATE  | GROUP                            | ART UNIT                   |                    |
| BY APPLICANT                |  | May 6, 2004   |  | 2813                             |                            |                    |
|                             |  | Ų,            | S. PATENT DOCUMENTS  |                                  |                            | ·                  |
| RXAMINER<br>INITIALS        | DOCUMENT<br>NUMBER                                   | DATE .        | NAME   | CLASS                            | SUB<br>CLASS               | FILING<br>DATE     |
|                             |  | ·             |  |                                  |                            | ļ                  |
|                             |  | FOR           | EIGN PATENT DOCUMENTS  |                                  | <del></del>                | ı                  |
| EXAMINER                    | DOCUMENT   | 7.0           |  |                                  | SUB                        | TRANSLATY<br>YEARO |
| INITIALS                    | NUMBER   | DATE          | COUNTRY  | CLASS                            | CLASS                      | 12340              |
|                             |  |               |  |                                  |                            |                    |
|                             |  |               |  |                                  |                            |                    |
|                             |  |               |  | <del></del>                      |                            |                    |
| . 1                         |  |               | Including Author, Title, Date, Pertinen<br>DRAM Cell", Kuo et al., IEEE Elec                           |                                  | attors Va                  | . 22 No            |
| 4)                          | 6, June 2002, pp.:                                   |               | DRAW CEIL, NGO ELBIL, ICEE CIEL  | Mon Device L                     | - <del></del>              | u. 23, 140.        |
|                             | "A Capacitoriess (<br>2002, pp.843-946               |               | DRAM Cell for High Density Appli   | cations*, Kuo                    | et al., IEE                | E IEDM,            |
|                             |  |               | SOI-NMOS Transistors at Low Te<br>rkshop (Sea Palms Resort, St. Sl                                     |                                  |                            |                    |
|                             |  |               | lied Memory Effect in SOI MOS 1<br>on Electron Devices, Vol. 37, No.                                   |                                  |                            |                    |
|                             | DRAMs", Villaret e                                   | t at, Procee  | lation in the Floating Body of Trip<br>dings of the INFOS 2003, Inst<br>tual Conference, June 18-20, 2 | lating Films                     | on                         |                    |
| 1 [                         | "A Memory Using<br>Embedded DRAM<br>Papers, June 200 | 's", Ohsawa e | or Gain Cell on SOI (FBC) with Prot al., 2003 Symposium on VLSI (                                      | erformance Si<br>Circuita Digest | uitable for<br>t of Trichn | ical               |
|                             |  |               | mbedded DRAM on SOI, Inch et pers, June 2003 (2 pages)   | al., 2003 Sym                    | posium oi                  | n VLSI             |
| (h)                         | Toshiba's DRAM                                       | Cell Piggybac | oks on SOI Wafer", Y. Hara, EE T   | imes, June 2                     | 003                        |                    |
|                             |  |               |  |                                  |                            |                    |
| XAMINER                     | SON DIN  | 111           | DATE CONSIDERED  | 12/9/0                           | 4                          |                    |



|   |   | · · · · · · · · · · · · · · · · · · ·   | ATTY. DOCKET NO.  | SERIAL   | NUMBER  | Sheet 2 of                      |
|---|---|---|---|--|---|---------------------------------|
|   | PTO-1449 (Modified)   | ٠.  | 211.004-US  |  | 10/840,0  | 09                              |
|   | PARTMENT OF COM<br>FAND TRADEMARK   |   | APPLICANT(S) Ferrant et al.   |  |   |                                 |
| INPODMAT                                      | א אפוופר מפנו   | TATEMENT  | FILING DATE   | GROUP  | ART UNIT  |                                 |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT |   | May 6, 2004   |   | 2818   |   |                                 |
|   |   | Ü.  | S. PATENT DOCUMENTS   | <del></del>  |   |                                 |
| examiner<br>Initials                          | DOCUMENT<br>NUMBER  | DATE  | NAME  | CLASS  | SUB<br>CLASS  | FILING<br>DATE                  |
|   | <u> </u>  |   |   |  |   |                                 |
|   | •   |   |   |  |   |                                 |
|   |   | FÖR   | EIGN PATENT DOCUMENTS   |  |   |                                 |
| EXAMINER<br>INITIALS                          | DOCUMENT<br>NUMBER  | DATE  | COUNTRY   | CLASS  | St B<br>Cl_as9  | TRANSLATION<br>YESHO            |
|   |   |   |   |  |   |                                 |
|   |   |   | **************************************  |  |   |                                 |
|   |   |   |   | A Pages (Str.)   |   |                                 |
| 51)   | "Memory Design  | Using a One-1   | Including Author, Title, Date, Pertinen<br>Fransistor Gain Cell on SOI", Ohs<br>November 2002, pp.1510-1522   |  | EE Journa   | l of Solid-                     |
| 1   | *Opposite Side Fl   | oating Gate S   | OI FLASH Memory Cell", Lin et a   | I., IEEE, Mar  | th 2000, p  | p.12-15                         |
|   | "Advanced TFT S<br>Transactions on 8  | RAM Cell Tec<br>lectron Devic   | hnology Using a Phase-Shift Lith<br>es, Vol. 42, No. 7, July 1995, pp.  | ogrephy", Ya<br>1305-1313  | maneka el   | al., IEEE                       |
|   | "Soft-Error Charge  | cteristics in Bi  | polar Memory Cells with Small Ci  | ritical Charge   | ldei et al  |                                 |
| .   |   |   | es, Val. 38, No. 11, November 16  |  |   | ., IEEE                         |
| .   | Transactions on E   | etors Self-Refr   |   | 991, pp.2465-  | 2471  |                                 |
|   | "An SOI 4 Transis<br>2003, pp.401-404<br>"Design of a SOI   | Electron Devic  | es, Val. 38, No. 11, November 16  | 991, pp.2465-<br>cell. Thomas<br>International   | et al. IEE  | E, March<br>ce on               |
|   | "An SOI 4 Transis<br>2003, pp.401-404<br>"Design of a SOI<br>Microelectronics (   | itors Self-Refr<br>Memory Cell*,<br>MIEL '97), Vo   | es, Val. 38, No. 11, November 16 esh Ultra-Low-Voltage Memory C Stanojevic et al., IEEE Proc. 21  | ell", Thomas International embar 1997, j   | et al. IEE  Comeren  op.297-300  atile Memo   | E, March<br>ce on               |
|   | "An SOI 4 Transis<br>2003, pp.401-404<br>"Design of a SOI<br>Microelectronics (<br>"Effects of Floatin<br>Chan et al., IEEE   | itors Self-Refr<br>Memory Cell",<br>MIEL '97), Vo<br>g Body on Do<br>Electron Devi  | es, Val. 38, No. 11, November 16 esh Ultra-Low-Voltage Memory C Stanojevic et al., IEEE Proc. 216 l. 1, NIS, Yugoslavis, 14-17 Septe uble Polysilicon Partially Deplete   | ell, pp.2465-<br>cell, Thomas<br>International<br>ember 1997, j<br>d SOI Nonvol<br>ary 2003, pp.7  | et al. IEE  Comeren pp.297-300 atile Memo   | E, March<br>ce on               |
|   | "An SOI 4 Transis 2003, pp.401-404 "Design of a SOI Microelectronics ( "Effects of Floatin Chan et al., IEEE "MOSFET Design" "One of Application  | Memory Cell",<br>MIEL '97), Vo<br>g Body on Do<br>Electron Devi   | es, Val. 38, No. 11, November 16 esh Ultra-Low-Voltage Memory C Stanojevic et al., IEEE Proc. 21 <sup>6</sup> I. 1, NIS, Yugoslavis, 14-17 Septe uble Polysilicon Partially Deplete ce Letters, Vol. 24, No. 2, Februa  | ell, pp.2465-<br>cell, Thomas<br>International<br>embar 1997, pd SOI Norvol<br>ary 2003, pp.7<br>14, 2002 (3 pa<br>ir et al., IEEE                       | et al. IEE  Comieren pp.297-300 atile Memo 5-77 pges)  Proc. 22 <sup>nd</sup>                 | E, March<br>ce on<br>ory Cell". |
|   | Transactions on E  "An SOI 4 Transis 2003, pp.401-404  "Design of a SOI Microelectronics (  "Effects of Floatin Chan et al., IEEE  "MOSFET Design  "One of Applicatio International Cont pp.458-458  "A SOI Current Miles of Source of Miles | Memory Cell", MIEL '97), Vo g Body on Do Electron Devi simplifies DF on of SOI Mem ference on Mide  | es, Vol. 38, No. 11, November 16 esh Ultra-Low-Voltage Memory C Stanojevic et al., IEEE Proc. 21 <sup>6</sup> I. 1, NIS, Yugoslavis, 14-17 Septe uble Polysilicon Partially Deplete ce Letters, Vol. 24, No. 2, Fabrua RAM*, P. Fazan, EE Times, May 1 tory Cell – Memory Array*, Lonca   | ell, pp.2465-<br>cell, Thomas<br>International<br>ember 1997, j<br>d SOI Nonvol<br>ary 2003, pp.7<br>14, 2002 (3 pa<br>ir et al., IEEE<br>2, NIŠ, Serbia | ct al. IEE  Comeren  pp.297-300  atile t/lemx  5-77  ages)  Proc. 22 <sup>nd</sup> , 14- 7 Ma | E, March ce on ony Cell".       |
| \$\frac{1}{4}\$                               | Transactions on E  "An SOI 4 Transis 2003, pp.401-404  *Design of a SOI Microelectronics (  "Effects of Floatin Chan et al., IEEE  "MOSFET Design  "One of Applicatio International Confup. 455-458  "A SOI Current MilEEE International "Chip Level Relial   | Memory Cell", MIEL '97), Vo g Body on Do Electron Devi Simplifies DF on of SOI Mem ference on Mid emory for Ana il SOI Confere billity on SOI E | es, Vol. 38, No. 11, November 16 esh Ultra-Low-Voltage Memory C Stanojevic et al., IEEE Proc. 21 <sup>6</sup> I. 1, NIS, Yugoslavis, 14-17 Septe uble Polysilicon Partially Deplete ce Letters, Vol. 24, No. 2, Februa IAM", P. Fazan, EE Times, May 1 hory Cell – Memory Array", Lonca croelectronics (MIEL 2000), Vol. 2 log Signal Processing at High Te | ell", Thomas  International ember 1997, j  SOI Nonvol ary 2003, pp.7  14, 2002 (3 pa ir et al., IEEE 2, NIS, Serbia                                      | et al. IEE  Comeren pp.297-300 atile Memo 5-77 ages)  Proc. 22 <sup>nd</sup> , 14- 7 Ma       | E, March ce on ony Cell".       |

|                      |  |                                      |                            |  |                                |                           | She             | et 3 of         |
|----------------------|--|--------------------------------------|----------------------------|--|--------------------------------|---------------------------|-----------------|-----------------|
|                      | PTO-1449 (Medified)  |                                      |                            | OCKET NO.  | \$ERJAL                        | NUMBER                    |                 |                 |
|                      | ( CO-1745 (Madilled)   |                                      | L                          | 211.004-US   |                                | 10/840,0                  | 09              |                 |
|                      | PARTMENT OF COM<br>I AND TRADEMARK                           |                                      | APPLICA                    | NT(S)  |                                |                           |                 |                 |
| rain1                | I AND I KAIMAAA  | OFFICE                               |                            | Ferrant et al.                                     |                                |                           |                 | •               |
| DIFOR A              | 10N disclosure s   | T 4 TE\ 1 E N T                      | FILING D                   | ATE  | GROUP                          | ART UNIT                  |                 |                 |
| HITORINAL            | BY APPLICANT   | IN I DIVIDIN                         | 1                          | May 6, 2004  |                                | 2818                      |                 |                 |
|                      |  | 1:0                                  | DATES OF                   | ACCTUATE NEED                                      | <del></del>                    |                           |                 |                 |
|                      | T  | T                                    | . PAIENI L                 | OCUMENTS   | T                              | 1                         |                 |                 |
| FXAMINER<br>INITIALS | DOCUMENT<br>NUMBER   | DATE                                 |                            | NAME   | CLASS                          | SUB                       | PIL             | INC<br>FR       |
|                      |  |                                      |                            |  |                                |                           |                 |                 |
|                      | <del> </del>   |                                      |                            |  |                                |                           | $\vdash$        |                 |
|                      | <u> L</u>  | ll                                   |                            | <del></del>  |                                | <u></u>                   |                 |                 |
|                      | ,  | FORE                                 | ign paten                  | T DOCUMENTS  | <del></del>                    | <del></del>               |                 |                 |
| EXAMINER             | DOCUMENT   | J                                    |                            |  |                                | SLB                       | TRANS           | SLATION<br>SUIC |
| INITIALS             | NUMBER   | DATE                                 |                            | COUNTRY  | CLASS                          | CLASS                     |                 | _               |
|                      |  |                                      |                            |  | 1 1                            | İ                         |                 |                 |
|                      |  |                                      |                            |  |                                |                           |                 |                 |
|                      |  |                                      |                            | <del></del>  | 1                              |                           |                 |                 |
| <del></del>          |  |                                      |                            | hor, Title, Date, Pertisent                        |                                |                           |                 |                 |
| 41)                  | "Analysis of Floati<br>Proceedings 1998                      | ng-Body-Induc<br>IEEE Internat       | ed Leakag<br>ional SCI C   | e Current in 0,15µ m \$<br>conference, Oct. 1998,  | OI DRAM",<br>pp.138-139        | Terauchi e                | t al            |                 |
|                      | *Programming and<br>Fabricated on SO<br>1995, pp.129-130     | Wafers", Chi                         | oating-Bod<br>et al., Proc | y for High Density Lov<br>eedings 1995 IEEE In     | v Voltage Fla<br>ternational S | sh EEPRO<br>OI Confer     | OM<br>ence,     | Oct.            |
|                      | "Measurement of<br>Electron Device L                         | Transient Effect<br>etters, Vol. 17, | ots in SOI D<br>No. 5, May | PRAM/SRAM Access 7<br>1998, pp.193-195             | ransistors",                   | A. Wai, IE                | EE              |                 |
|                      | "In-Depth Analysis<br>Defect Creation at<br>1995, pp.383-388 | nd Annihilation                      | Channel Ba<br>", Sinha et  | sed Charge Injection i<br>al., Elsevier Science, I | n SOI MOSF<br>Microelectror    | ETs and F<br>nic Engine   | lelate<br>ering | d<br>28,        |
|                      | "Dynamic Effects   | in SOI MOSFE                         | T's", Giffan               | d et al., IEEE, 1991, p                            | p.180-161                      |                           |                 |                 |
|                      |  |                                      |                            | nory Cell for High Perfo<br>Circuits Conference,   |                                |                           | RAM             |                 |
|                      | "A Novel Pattern 1<br>IEEE International                     |                                      |                            | ed SOI Giga-bit DRAN<br>98, pp.114-115             | /is", Lee et al                | ., Ртосеес                | egráf           | 1996            |
|                      | *An Experimental Furuyama et al., Il                         | 2-bit/Cell Store                     | ge DRAM                    | for Macrocell or Memo<br>e Circuits, Vol. 24, No.  | ry-on-Logic /<br>2, April 1989 | Application<br>9, pp.388- | )*,<br>393      |                 |
|                      | "High-Performance  | e Embedded S<br>of Solid-State (     | OI DRAM ,<br>Circults, Vol | Architecture for the Lo<br>1. 35, No. 8, August 20 | w-Power Sup<br>00, pp.1169-    | ply", Yam<br>1178         | auchi           | et              |
|                      |  |                                      |                            | e Range by CMOS/611<br>Conference, pp.138-         |                                | logy", Sur                | na et           | al.,            |
| 40                   | "A Capacitoriess I   | RAM Cell on                          | SOI Substr                 | ate", Wann et al., IEEE                            | E IEDM, 1993                   | 3, pp.535-                | 538             |                 |
|                      |  |                                      |                            |  |                                |                           |                 |                 |
| EXAMINER             | SON DI   | V H                                  | D,                         | ATE CONSIDERED                                     | 2/9/04                         |                           |                 |                 |
| EXAMINER: 1          | aitial citation if referen                                   | ce was considered                    | d. Draw line               | through eitation if ant la                         | conformance to                 | MPE# 609                  | and no          | ı <b>t</b>      |

6509688102

|            |  |  |  |  |  | - She   | et 4 of      |
|------------|--|--|--|--|--|---|--------------|
|            | PTO-1449 (Modified)  |  | ATTY. DOCKET NO.   | SERIAL   | NIIMBER  |   |              |
|            | •  | •  | 211.004-US   |  | 10/840,0   | 09  |              |
|            | PARTMENT OF CON<br>FAND TRADEMARK  |  | APPLICANT(S)  Ferrant et al.   |  |  |   |              |
| N.EODM . W | INFORMATION DISCLOSURE STATEMENT<br>BY APPLICANT   |  | FILING DATE  | GROUP  | ART UNIT   |   |              |
| INPURMAT   |  |  | May 6, 2004  |  | 2818   |   |              |
|            |  | Ų.:  | S. PATENT DOCUMENTS  |  |  |   |              |
| EXAMINER   | DOCUMENT   | DATE   | NAME   |  | SUB  | FIL.  | ING          |
| INITIALS   | NUMBER   |  |  | CLASS  | CLASS  | DAT   |              |
|            |  |  |  |  |  |   |              |
|            |  |  |  | ]  |  |   |              |
|            |  | FORE   | IGN PATENT DOCUMENTS   |  |  |   |              |
| EXAMINER   | DOCUMENT   |  |  |  | SUB  | TRAIN   | 1100<br>1100 |
| Initials   | NUMBER   | DATE   | COUNTRY  | CLASS  | CLASS  |   |              |
|            |  | ·  |  |  |  |   |              |
|            |  |  |  |  |  |   |              |
|            | OTHER 1  | DOCUMENTS (I   | nelading Author, Titta, Date, Pertin   | ent Pages, Etc.)   |  |   |              |
| 41)        | "The Multistable (<br>et al., IEEE Work<br>Burlington, pp.13"  | shop on Low T  | led Memory Effect in SOI Tran<br>emperature Electronics, 7-8 A   | sistors at Low T<br>ug. 1989, Unive  | emperatursity of Ve  | res".<br>rmoni                                | rack<br>.,   |
|            | Application*, Wan  | Ultra-Thin Tun<br>ın et al., IEEE I  | nel Oxide in MONOS Device S<br>Electron Device Letters, Vol. 1   | Structure for Dyr<br>B, No. 11, Nove   | namic Men  | nary<br>5, pp.4                               | 191-         |
| l í        | 493  |  |  | •  |  |   |              |
|            |  |  | Fully Depleted SOI MOSFET's  |  |  |   | ice          |
|            | "Hot-Carrier Effect<br>Letters, Vol. 15, N   | of Thin-Body S   | 94, pp.218-220<br>Bilcide Source/Drain Devices",   | 3°, Ma et al., IEE   | EE Electro   | n Dev   | ice          |
|            | "Hot-Carrier Effec<br>Letters, Vol. 15, N<br>"Design Analysis<br>Conference, Octo  | of Thin-Body S<br>ber 2001, pp.2   | 94, pp.218-220<br>Bilcide Source/Drain Devices",   | 3°, Ma et al., IEE<br>2001 IEEE Inte   | EE Electro   | n Dev   | ice          |
|            | "Hot-Carrier Effectetters, Vol. 15, No. 15, No | to. 6, June 199 of Thin-Body S ber 2001, pp.2 Low Cost SPI   | 94, pp.218-220<br>Blicide Source/Drain Devices",<br>11-22  | 3°, Ma et al., IEE<br>2001 IEEE Inte<br>EE IEDM, Septe   | EE Electro   | n Dev   |              |
|            | "Hot-Carrier Effect Letters, Vol. 15, No. 15,  | to. 6, June 198 of Thin-Body 8 ber 2001, pp.2 Low Cost SPI ating Body Effi (IEEE Cat No. port of inversion   | 94, pp.218-220  Blicke Source/Drain Devices*, 11-22  MOX Substrate*, lyer et al., IEI  ect In SOI Circuits Using BSIM  | 2001 IEEE Inte<br>EE IEDM, Septe<br>3SOI*, Tu et al.   | EE Electro   | n Dev   | 1            |
|            | "Hot-Carrier Effect Letters, Vol. 15, No. 15,  | to. 6, June 199 of Thin-Body S ber 2001, pp.2 Low Cost SPI ating Body Effi (IEEE Cat No. port of Inversion, IEEE Transa  | MA, pp.218-220  Glicide Source/Drain Devices*, 11-22  MOX Substrate*, lyer et al., IE  ect In SOI Circuits Using BSIM 97 <sup>TM</sup> 8303), pp.339-342  on-Layer Electrons and Holes II  | 2001 IEEE Inte 2001 IEEE Inte EE IEDM, Septe 3SOI", Tu et al. Including Veloch   | rnational Sember 199 , Proceeding Overshood 1997, pp.                        | n Dev<br>SOI<br>8,<br>ngs o:<br>ot",<br>p.684 | 671          |
|            | "Hot-Carrier Effectetters, Vol. 15, No. 15, No | to. 6, June 198 of Thin-Body S ber 2001, pp.2 Low Cost SPI ating Body Effi (IEEE Cat No. port of Inversio IEEE Transa old-Voltage MC s on Electron L ced Degradatio                                      | M4, pp.218-220  Blicide Source/Drain Devices*, 21-22  MOX Substrate*, lyer et al., IEI  ect In SOI Circuits Using BSIM 97 <sup>TM</sup> 8303), pp.339-342  on-Layer Electrons and Holes II ctions on Electron Devices, Vo  | 2001 IEEE Inte<br>2001 IEEE Inte<br>EE IEDM, Septe<br>3SOI", Tu et al.<br>nctuding Velocit<br>II. 44, No. 4, Ap<br>Voltage VLSI",<br>1997, pp.414-4                  | rnational Sambe 199 , Proceedi y Overshould 1997, p Assadera                 | n Dev<br>SOI<br>8,<br>ngs of<br>ot",<br>p.684 | 671          |
| 40         | "Hot-Carrier Effectetters, Vol. 15, No. 15, No | to. 6, June 199 of Thin-Body S ber 2001, pp.2 Low Cost SPI ating Body Effi (IEEE Cat No. port of Inversion, IEEE Transa old-Voltage MC s on Electron L ced Degradation onlics, Vol. 39, t in Ultra-Thin- | MA, pp.218-220  Blicide Source/Drain Devices*, 11-22  MOX Substrate*, lyer et al., IEI  ect In SOI Circuits Using BSIM. 97 <sup>TM</sup> 8303), pp.339-342  on-Layer Electrons and Hofas II ctions on Electron Devices, Vol. 25FET (DTMOS) for Ultra-Low Devices, Vol. 44, No. 3, March in in Ultra-Thin-Film Fully-Depl | 2001 IEEE Inte<br>2001 IEEE Inte<br>EE IEDM, Septe<br>3SOI", Tu et al.<br>ncluding Velocit<br>il. 44, No. 4, Ap<br>Voltage VLSI",<br>1997, pp.414-4<br>eted SOI MOSF | rnational Sambe 199 , Proceeding Overshould 1997, pp. Assaderage 22 ETs", Yu | n Dev<br>SOI<br>8,<br>ngs o'<br>t',<br>p.684  | 671<br>al.,  |



|                      |   |  |  |   |  | VPT   | 5 of             |
|----------------------|---|--|--|---|--|---|------------------|
|                      | PTO-1449 (Modified  | ````   | ATTY. DOCKET NO.   | SERIAL  | NUMBER   |   |                  |
| ue be                | PARTMENT OF COR   | •  | 211.004-US   |   | 10/840,0   | 09  |                  |
|                      | AND TRADEMARI   |  | APPLICANT(S)  Ferrant et al.   |   |  |   |                  |
| INFORMAT             | RMATION DISCLOSURE STATEMENT  |  | IN DISCLOSURE STATEMENT FILING DATE GROUP ART  |   |  |   |                  |
|                      | BY APPLICANT  |  | May 6, 2004  |   | 2818   |   |                  |
|                      | <del></del>   | <u>u</u>   | S. PATENT DOCUMENTS  |   |  |   |                  |
| EXAMINER<br>INITIALS | DOCUMENT<br>NUMBER  | DATE   | NAME   | CLASS   | SUB<br>CLASS   | FILIN<br>DATE   | -                |
|                      |   |  |  |   |  |   |                  |
|                      | <u> </u>  |  |  |   |  | <u> </u>  |                  |
|                      |   | FOR  | EIGN PATENT DOCUMENTS  |   |  |   |                  |
| EXAMINER<br>INITIALS | DOCUMENT<br>NUMBER  | DATE   | COUNTRY  | CLA\$9  | S1;B<br>CLASS  | TRAFSIA<br>VENE   | .TIEP            |
|                      |   |  |  |   |  |   |                  |
|                      |   |  |  |   |  |   |                  |
|                      | <del></del>   | · · · · ·  |  |   |  |   |                  |
|                      | OTHER   | DOCUMENTS (  | (Including Author, Title, Date, Pertin   | ent Pages, Etc.)  |  |   |                  |
| GD                   | "SOI MOSFET D   | esign for Ali-D  | (Including Author, Title, Date, Pertia<br>timensional Scaling with Short C<br>1, 1995, pp.631-634  |   | width an   | d Ultra-  | thin             |
| CD                   | "SOI MOSFET DE<br>Films", Chan et a<br>"A Novel Silicon-  | esign for Ali-D<br>it., IEEE IEDM<br>On-insulator (1   | imensional Scaling with Short C  | channel, Narrov   | •  |   |                  |
| 40                   | "SOI MOSFET DI<br>Films", Chan et a<br>"A Novel Silicon-<br>1994 IEEE Symp<br>"Interface Charac   | esign for Ali-D<br>it., IEEE IEDM<br>On-Insulator (Sosium on Low<br>Sterization of F   | timensional Scaling with Short C<br>I, 1995, pp.631-834<br>SOI) MOSFET for Ultra Low Vol   | tage Operation  | ", Assader   | aghi et   | BÌ.,             |
| CP)                  | "SOI MOSFET DI<br>Films", Chan et a<br>"A Novel Silicon-<br>1994 IEEE Symp<br>"Interface Charac<br>al., Proceedings"  | esign for All-Dail., IEEE IEOM On-Insulator (iosium on Low Iterization of F 1994 IEEE Int  | timensional Scaling with Short C<br>I, 1995, pp.631-634<br>SOI) MOSFET for Ultra Low Vol<br>Power Electronics, pp.68-59  | tage Operation a Subthreshold   | ", Assader   | aghi et   | el.,             |
| CD                   | "SOI MOSFET DI<br>Films", Chan et a<br>"A Novel Silicon-<br>1994 IEEE Symp<br>"Interface Charac<br>al., Proceedings<br>"A Capacitorless<br>IEDM, Feb. 2002<br>"A Dynamic Three  | esign for All-Dat., IEEE IEDM On-Insulator (sosium on Low sterization of F 1994 IEEE Int. Double-Gate I., pp.843-846 shold Voltage   | timensional Scaling with Short C<br>1, 1995, pp.631-834<br>SOI) MOSFET for Ultra Low Vol<br>Power Electronics, pp.68-59<br>Fully-Depleted SOI MOSFET by<br>ternational SOI Conference, Oct   | tage Operation a Subthreshold 1994, pp.63-6 sity Application  | ", Assader I-V Method 4 us", Kuo et  | aghi et<br>od", Yu<br>al., IEE                                    | et.              |
| CP)                  | "SOI MOSFET DI<br>Films", Chan et a<br>"A Novel Silicon-<br>1994 IEEE Symp<br>"Interface Charac<br>al., Proceedings<br>"A Capacitorless<br>IEDM, Feb. 2002<br>"A Dynamic Three<br>et al., IEEE Elect  | esign for All-D<br>it., IEEE IEOM<br>On-Insulator (i<br>osium on Low<br>Iterization of F<br>1994 IEEE Int<br>Double-Gate<br>, pp.843-846<br>shold Voltage<br>ron Device Le   | timensional Scaling with Short Co., 1995, pp.631-834  SOI) MOSFET for Ultra Low Vol. Power Electronics, pp.68-59  Fully-Depleted SOI MOSFET by ternetional SOI Conference, Oct. DRAM Cell Design for High Den. MOSFET (DTMOS) for Ultra-Low ters, Vol. 15, No. 12, December 10SFET (DTMOS) for Ultra-Low 10SFET (D | tage Operation a Subthreshold 1994, pp.63-6 sity Application w Voltage Ope r 1994, pp.510-  | ", Assader  I-V Method  4  s", Kuo et  ration", As 512   | aghi et<br>d", Yu<br>al., IEE<br>sadera                           | et.<br>E         |
| CP)                  | "SOI MOSFET DI<br>Films", Chan et a<br>"A Novel Silicon-<br>1994 IEEE Symp<br>"Interface Charac<br>al., Proceedings<br>"A Capacitorless<br>IEDM, Feb. 2002<br>"A Dynamic Three<br>et al., IEEE Elect<br>"Dynamic Thresh<br>al., 1994 EEE, IE  | esign for All-Dat., IEEE IEDM On-Insulator (sosium on Low sterization of F 1994 IEEE Int. Double-Gate i., pp.843-846 shold Voltage ron Device Le old-Voltage M DM 94, pp.80  | timensional Scaling with Short Co., 1995, pp.631-834  SOI) MOSFET for Ultra Low Vol. Power Electronics, pp.68-59  Fully-Depleted SOI MOSFET by ternetional SOI Conference, Oct. DRAM Cell Design for High Den. MOSFET (DTMOS) for Ultra-Low ters, Vol. 15, No. 12, December 10SFET (DTMOS) for Ultra-Low 10SFET (D | tage Operation a Subthreshold 1994, pp.63-6 sity Application w Voltage Oper r 1994, pp.510-   | ", Assader  I-V Method  4  Is", Kuo et  ration", Assa  | aghi et<br>d", Yu<br>al., IEE<br>sadera                           | et<br>E          |
| CP)                  | "SOI MOSFET DI<br>Films", Chan et a<br>"A Novel Silicon-<br>1994 IEEE Symp<br>"Interface Charac<br>al., Proceedings<br>"A Capacitorless<br>IEDM, Feb. 2002<br>"A Dynamic Three<br>et al., IEEE Elect<br>"Oynamic Thresh<br>al., 1994 EEE, IE<br>"A Capacitorless<br>"Studying the Imp   | esign for All-Dat., IEEE IEDM On-insulator (fosium on Low sterization of F1994 IEEE Int Double-Gate Int Double | timensional Scaling with Short Co., 1995, pp.631-634  SOI) MOSFET for Ultra Low Volve Power Electronics, pp.68-59  Fully-Depleted SOI MOSFET by ternational SOI Conference, Oct.  DRAM Cell Design for High Den.  MOSFET (DTMOS) for Ultra-Low 19-812  IN SOI Substrate", Wann et al., If tunneling on Dynamic Bahaviors 19-19-19-19-19-19-19-19-19-19-19-19-19-1  | tage Operation  a Subthreshold 1994, pp.63-6  sity Application  w Voltage Oper 1994, pp.510  Voltage Opera  EEE IEDM 1993  of Partially-De                              | ", Assader  I-V Method  s", Kuo et  ration", Assation", Assation", Assation", Assation                                 | aghi et<br>ed", Yu<br>al., IEE<br>sadera<br>ederagh               | et.              |
| CD                   | "SOI MOSFET DIFILMS", Chan et a "A Novel Silicon- 1994 IEEE Symp "Interface Charac al., Proceedings "A Capacitorless IEDM, Feb. 2002 "A Dynamic Three et al., IEEE Elect "Oynamic Thresh al., 1994 EEE, IE "A Capacitorless "Studying the Impusing BSIMPD", Design (ISQED 'C  | esign for All-Dait., IEEE IEDM On-Insulator (sosium on Low sterization of F1994 IEEE Int Double-Gate i., pp.843-846 shold Voltage ron Device Le old-Voltage M DM 94, pp.80: DRAM Cell or Dact of Gate T. Su et al., IEEE D2), April 2002 of Front and I by the Charge  | timensional Scaling with Short Co., 1995, pp.631-634  SOI) MOSFET for Ultra Low Volve Power Electronics, pp.68-59  Fully-Depleted SOI MOSFET by ternational SOI Conference, Oct.  DRAM Cell Design for High Den.  MOSFET (DTMOS) for Ultra-Low 19-812  IN SOI Substrate", Wann et al., If tunneling on Dynamic Bahaviors 19-19-19-19-19-19-19-19-19-19-19-19-19-1  | tage Operation a Subthreshold 1994, pp.63-6 sity Application w Voltage Opera 1994, pp.510 Voltage Opera EEE IEDM 1993 of Partially-De al Symposium et al., IEEE Tre     | ", Assader  I-V Method  s", Kuo et  ration", Assation", Assation", Assation", Assation, Assation Quality  s Silicum-or | aghi et  od", Yu  al., IEE  saderagh  deragh  CMOS  Electro       | al., et ghi i et |
| GD                   | "SOI MOSFET DEFILMS", Chan et a "A Novel Silicon- 1994 IEEE Symp "Interface Charac al., Proceedings "A Capacitorless IEDM, Feb. 2002 "A Dynamic Three et al., IEEE Elect "Oynamic Thresh al., 1994 EEE, IE "A Capacitorless "Studying the Imp Using BSIMPD", Design (ISQED 'C "Characterization MOS Structures t Electron Devices | esign for All-Dat., IEEE IEDM On-Insulator (sosium on Low sterization of Fi 1994 IEEE Int. Double-Gate I., pp.843-846 shold Voltage fron Device Le old-Voltage MDM 94, pp.801 DRAM Cell or Deact of Gate To Su et al., IEEE 12), April 2002 of Front and I by the Charge Vol. 38, No. 1 del for the Min  | timensional Scaling with Short Co., 1995, pp.631-634  SOI) MOSFET for Ultra Low Vol. Power Electronics, pp.68-59  Fully-Depleted SOI MOSFET by ternational SOI Conference, Oct. DRAM Cell Design for High Der. MOSFET (DTMOS) for Ultra-Low ters, Vol. 15, No. 12, December 100 SPET (DTMOS) for Ultra-Low 9-812  In SOI Substrate", Wann et al., If unnelling on Dynamic Behaviors E Proceedings of the Internation (5 pages)  Back Si-SiO <sub>2</sub> Interfaces in Thick Pumping Technique", Wouters 9, September 1989, pp.1746-17   | tage Operation a Subthreshold 1994, pp.63-6 sity Application w Voltage Opera 1994, pp.510 Voltage Opera EEE IEDM 1983 of Partially-Depail Symposium et al., IEEE Tre 50 | ", Assader  I-V Method  s", Kuo et  ration", Assa  512  tion", Assa  pleted SO on Quality  s Silicum-or ansactions     | aghi et  ad", Yu  al., IEE  sadera  aderagh  sa8  I CMOS  Electro | al., et ghi i et |

6509688102



|  |  |   | ATTY. DOCKET NO.   | SERIAL   | NUMBER  | Sheet 6  |
|--|--|---|--|--|---|--|
|  | PTO-1449 (Modified)  | )   | 211.004-US   |  | 10/840,0  | <b>109</b>   |
|  | PARTMENT OF CON  |   | APPLICANT(S)   |  |   |  |
| PATEN  | i and trademark  | COPPICE   | Ferrant et al.   |  |   |  |
| Information disclosure statement<br>by applicant |  | FILING DATE   | GROUP  | ART JNT  |   |  |
|  |  | May 6, 2004   |  | 2818   |   |  |
|  |  | U.  | S. PATENT DOCUMENTS  |  |   |  |
| EXAMINER   | DOCUMENT   | DATE  | NAME   |  | SUB   | FILING   |
| INITIALS NUMBER                                  |  | CLASS   | C1.A59   | DATE   |   |  |
|  | ļ  | <u> </u>  |  |  | <u> </u>  | ļ  |
|  |  |   |  |  |   |  |
|  |  | FORI  | PIGN PATENT DOCUMENTS  |  |   | <del></del>  |
| EXAMINER   | DOCUMENT   |   | The state of the s |  | \$LB  | TRANSLATION<br>YEMAN   |
| INITIALS   | NUMBER   | DATE  | COUNTRY  | CLASS  | CLASS   | VERMO  |
|  |  | ,   |  |  |   |  |
|  |  |   |  |  |   |  |
| <del></del>                                      | <del></del>  | LI.   |  |  |   |  |
|  | OTHER  | DOCUMENTS (I  | including Anthor, Title, Date, Pertine   | nt Pages, Etc.)  |   |  |
| 1  |  |   |  |  |   |  |
| SD   |  |   | AM with the Body Refresh Fund<br>o. 7, July 1997, pp.899-904   | ction", Tomishi  | ma et al., I  | EICE   |
| SD   | Trans. Electron., \ "A Simple 1-Trans  | Vol. E80-C, No<br>sistor Capacito   | AM with the Body Refresh Fund  | erformance Em  | bedded D  |  |
| SD   | Trans. Electron., \ "A Simple 1-Trans Fazan et al., IEEE "High-Endurance   | Vol. E80-C, No<br>sister Capacito<br>E 2002 Custom<br>Ultra-Thin Tun  | AM with the Body Refresh Fund<br>. 7, July 1997, pp.899-904<br>pr-Less Memory Cell for High Pe   | erformance Em<br>e, June 2002, p<br>tructure for Dys   | bedded D<br>p.99-102<br>namic Mer   | RAMs".   |
| SD   | Trans. Electron.,  "A Simple 1-Trans Fazan et al., IEEE  "High-Endurance Application", Wan 493   | Vol. E80-C, No<br>sistor Capacito<br>E 2002 Custor<br>Ultra-Thin Tun<br>in et al., IEEE   | tAM with the Body Refresh Fund<br>p. 7, July 1997, pp.899-904<br>pr-Less Memory Cell for High Per<br>integrated Circuits Conference<br>and Oxide in MONOS Device Si  | erformance Em<br>e, June 2002, p<br>tructure for Dyr<br>i, No. 11, Nove  | bedded D<br>p.99-102<br>namic Mer<br>imber 199  | RAMs".<br>nory<br>5, pp.491-                                 |
| SD   | Trans. Electron.,  "A Simple 1-Trans Fazan et al., IEEE  "High-Endurance Application", Wan 493  "Capacitor-Less 1 2002, pp.10-13  "SOI (Silicon-on-lie   | Vol. E80-C, No<br>sistor Capacito<br>E 2002 Custom<br>Ultra-Thin Tun<br>in et al., IEEE   | tAM with the Body Refresh Fund<br>b. 7, July 1997, pp.899-904<br>or-Less Memary Cell for High Pe<br>Integrated Circuits Conference<br>and Oxide in MONOS Device SI<br>Electron Device Letters, Vol. 16   | erformance Em<br>e, June 2002, p<br>tructure for Dyr<br>i, No. 11, Nove<br>international SC<br>egration", C. H                   | bedded D<br>pp.99-102<br>namic Mer<br>mber 199:<br>Di Confere                                       | RAMs".<br>nory<br>5, pp.491-<br>ence, Oct                    |
| SD .   | Trans. Electron.,  "A Simple 1-Trans  Fazan et al., IEEE  "High-Endurance  Application", Wan  493  "Capacitor-Less 1  2002, pp.10-13  "SOI (Silicon-on-le  Phys. Vol. 33 (196  "Source-Bias Dep  | Vol. E80-C, No<br>sistor Capacito<br>E 2002 Custom<br>Ultra-Thin Tun<br>in et al., IEEE<br>I-Transistor DF<br>Insulator) for H<br>B4) pp.385-365  | tAM with the Body Refresh Fund<br>b. 7, July 1997, pp.899-904<br>or-Less Memory Cell for High Per<br>Integrated Circuits Conference<br>and Oxide in MONOS Device St<br>Electron Device Letters, Vol. 16<br>RAM", Fazan et al., 2002 (EEE)  | erformance Emer, June 2002, p<br>tructure for Dyri<br>i, No. 11, Nove<br>international So<br>egration*, C. H                     | bedded D<br>pp.99-102<br>namic Mer<br>mber 199<br>DI Confere<br>u, Jph, J.                          | RAMs". nory 5, pp.491- ence, Oct. Appl.                      |
| SD   | Trans. Electron., \ "A Simple 1-Trans Fazan et al., IEEE  "High-Endurance Application", Wan  493 "Capacitor-Less 1  2002, pp.10-13 "SOI (Silicon-on-le  Phys. Vol. 33 (198  "Source-Bias Dep  Memory Cell Tran  3B, March 1998 "Suppression of P                     | Vol. E80-C, No<br>sister Capacitor<br>E 2002 Custom<br>Ultra-Thin Tun<br>in et al., IEEE<br>I-Transister DF<br>insulator) for Hi<br>94) pp.385-369<br>rendent Charge<br>sisters", Sim et<br>Parasitic Bipola<br>ation into Soun | AM with the Body Refresh Funda. 7, July 1997, pp.899-904  or-Less Memory Cell for High Per Integrated Circuits Conference and Oxide in MONOS Device SI Electron Device Letters, Vol. 16  RAM", Fazan et al., 2002 IEEE in the Period Circuits Conference and Oxide in MONOS Device SI Electron Device Letters, Vol. 16  RAM", Fazan et al., 2002 IEEE in the Period Circuits American Security 1994  e Accumulation in P+-Poly Gatest al., Jpn. J. Appl. Phys. Vol. 37  or Action In Ultra-Thin-Film Fully-ce/Drain Regions", Ohno et al.,   | erformance Em  e, June 2002, p  tructure for Dyn  i, No. 11, Nove  regration*, C. H  e SOI Dynamic  (1998) pp.126  -Depleted CMC | bedded D<br>pp.99-102<br>hamic Mer<br>mber 199<br>DI Confere<br>u, Jph. J.<br>Random<br>30-12i33, P | RAMs".  nory 5, pp.491- ence, Oct.  Appl.  Access ert 1, No. |
|  | Trans. Electron., \ "A Simple 1-Trans Fazan et al., IEEE  "High-Endurance Application", Wan  493 "Capacitor-Less 1  2002, pp.10-13 "SOI (Silicon-on-le  Phys. Vol. 33 (196  "Source-Bias Dep  Memory Cell Tran  3B, March 1998 "Suppression of P  by Ar-lon Implanta | Vol. E80-C, No<br>sister Capacitor<br>E 2002 Custom<br>Ultra-Thin Tun<br>in et al., IEEE<br>I-Transister DF<br>insulator) for Hi<br>94) pp.385-369<br>rendent Charge<br>sisters", Sim et<br>Parasitic Bipola<br>ation into Soun | AM with the Body Refresh Funda. 7, July 1997, pp.899-904  or-Less Memory Cell for High Per Integrated Circuits Conference and Oxide in MONOS Device SI Electron Device Letters, Vol. 16  RAM", Fazan et al., 2002 IEEE in the Period Circuits Conference and Oxide in MONOS Device SI Electron Device Letters, Vol. 16  RAM", Fazan et al., 2002 IEEE in the Period Circuits American Security 1994  e Accumulation in P+-Poly Gatest al., Jpn. J. Appl. Phys. Vol. 37  or Action In Ultra-Thin-Film Fully-ce/Drain Regions", Ohno et al.,   | erformance Em  e, June 2002, p  tructure for Dyn  i, No. 11, Nove  regration*, C. H  e SOI Dynamic  (1998) pp.126  -Depleted CMC | bedded D<br>pp.99-102<br>hamic Mer<br>mber 199<br>DI Confere<br>u, Jph. J.<br>Random<br>30-12i33, P | RAMs".  nory 5, pp.491- ence, Oct.  Appl.  Access ert 1, No. |
|  | Trans. Electron., \ "A Simple 1-Trans Fazan et al., IEEE  "High-Endurance Application", Wan  493 "Capacitor-Less 1  2002, pp.10-13 "SOI (Silicon-on-le  Phys. Vol. 33 (196  "Source-Bias Dep  Memory Cell Tran  3B, March 1998 "Suppression of P  by Ar-lon Implanta | Vol. E80-C, No<br>sister Capacitor<br>E 2002 Custom<br>Ultra-Thin Tun<br>in et al., IEEE<br>I-Transister DF<br>insulator) for Hi<br>94) pp.385-369<br>rendent Charge<br>sisters", Sim et<br>Parasitic Bipola<br>ation into Soun | AM with the Body Refresh Funda. 7, July 1997, pp.899-904  or-Less Memory Cell for High Per Integrated Circuits Conference and Oxide in MONOS Device SI Electron Device Letters, Vol. 16  RAM", Fazan et al., 2002 IEEE in the Period Circuits Conference and Oxide in MONOS Device SI Electron Device Letters, Vol. 16  RAM", Fazan et al., 2002 IEEE in the Period Circuits American Security 1994  e Accumulation in P+-Poly Gatest al., Jpn. J. Appl. Phys. Vol. 37  or Action In Ultra-Thin-Film Fully-ce/Drain Regions", Ohno et al.,   | erformance Em  e, June 2002, p  tructure for Dyn  i, No. 11, Nove  regration*, C. H  e SOI Dynamic  (1998) pp.126  -Depleted CMC | bedded D<br>pp.99-102<br>hamic Mer<br>mber 199<br>DI Confere<br>u, Jph. J.<br>Random<br>30-12i33, P | RAMs".  nory 5, pp.491- ence, Oct.  Appl.  Access ert 1, No. |
|  | Trans. Electron., \ "A Simple 1-Trans Fazan et al., IEEE  "High-Endurance Application", Wan  493 "Capacitor-Less 1  2002, pp.10-13 "SOI (Silicon-on-le  Phys. Vol. 33 (196  "Source-Bias Dep  Memory Cell Tran  3B, March 1998 "Suppression of P  by Ar-lon Implanta | Vol. E80-C, No<br>sister Capacitor<br>E 2002 Custom<br>Ultra-Thin Tun<br>in et al., IEEE<br>I-Transister DF<br>insulator) for Hi<br>94) pp.385-369<br>rendent Charge<br>sisters", Sim et<br>Parasitic Bipola<br>ation into Soun | AM with the Body Refresh Funda. 7, July 1997, pp.899-904  or-Less Memory Cell for High Per Integrated Circuits Conference and Oxide in MONOS Device SI Electron Device Letters, Vol. 16  RAM", Fazan et al., 2002 IEEE in the Period Circuits Conference and Oxide in MONOS Device SI Electron Device Letters, Vol. 16  RAM", Fazan et al., 2002 IEEE in the Period Circuits American Security 1994  e Accumulation in P+-Poly Gatest al., Jpn. J. Appl. Phys. Vol. 37  or Action In Ultra-Thin-Film Fully-ce/Drain Regions", Ohno et al.,   | erformance Em  e, June 2002, p  tructure for Dyn  i, No. 11, Nove  regration*, C. H  e SOI Dynamic  (1998) pp.126  -Depleted CMC | bedded D<br>pp.99-102<br>hamic Mer<br>mber 199<br>DI Confere<br>u, Jph. J.<br>Random<br>30-12i33, P | RAMs".  nory 5, pp.491- ence, Oct.  Appl.  Access ert 1, No. |



Sheet 7 of 7 SERIAL NUMBER ATTY, DOCKET NO. PTO-1449 (Modified) 211.004-US 10/840,009 U.S. DEPARTMENT OF COMMERCE APPLICANT(5) PATENT AND TRADEMARK OFFICE Ferrant et al. GROUP ART UNIT FILING DATE INFORMATION DISCLOSURE STATEMENT 2818 May 5, 2004 BY APPLICANT U.S. PATENT DOCUMENTS FILING SUB DOCUMENT DATE NAME **EXAMINER** CLASS DATE INITIALS NUMBER FOREIGN PATENT DOCUMENTS TRANSGLAT ROP SUB BXAMINER DOCUMENT CLASS COUNTRY CLASS NUMBER DATE INITIALS OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) \*Fully Isolated Lateral Bipotar-MOS Transistors Fabricated In Zone-Melting-Recrystallized Si Films Si on SiO2, Tsaur et al., IEEE Electron Device Letters, Vol. EDL-4, No. 8, August 1983, pp.269-271 "Silicon-On-Insulator Bipolar Transistors", Rodder et al., IEEE Electron Device Letters, Vol. EDL-4, No. 6, June 1983, pp. 193-195 "Characteristics and Three-Dimensional Integration of MOSFET's in Small-Grain LF'CVD Polycrystalline Silicon", Malhi et al., IEEE Transactions on Electron Devices, Vol. ED-32, No. 2, February 1985, pp.258-281 Triple-Wel nMOSFET Evaluated as a Capacitor-Less DRAM Cell for Nanoscala Low-Cost & High Density Applications\*, Villaret et al., Handout at Proceedings of 2003 Silicon Nancelectronics Workshop, June 8-9, 2003, Kyoto, Japan (2 pages) \*Mechanisms of Charge Modulation in the Floating Body of Triple-Wall NMOSFET Capacitor-less DRAMs", Villaret et al., Handout at Proceedings of INFOS 2003, June 18-20, 2003, Barcelone, Spain (2 pages) "Embedded DRAM Process Technology", M. Yamawaki, Proceedings of the Symposium on Semiconductors and Integrated Circuits Technology, 1998, Vol. 55, pp.38-43 "3-Dimensional Simulation of Turn-off Current in Partially Depleted SOI MOSFETs", Ikeda et al., IEIC Technical Report, Institute of Electronics, Information and Communication Engineers, 1998. Vol. 97, No. 557 (SDM97 186-198), pp.27-34 \*DRAM Design Using the Taper-Isolated Dynamic RAM Cell, Leiss et al.\*, IEEE Transactions on くわ Electron Devices, Vol. ED-29, No. 4, April 1982, pp.707-714 DATE CONSIDERED 12/9/04 EXAMINER SON DINH EXAMINER: Initial citation if reference was considered. Drow line through eltation if not in conformance to MPEP 609 and ant considered. Include copy of this form with next communication to applicant.



| 3   |                                       |             |                                       |                  |              |                    |
|---|---------------------------------------|-------------|---------------------------------------|------------------|--------------|--------------------|
| PTO-1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE |                                       |             | ATTY. DOCKET NO.<br>211.004-US        | SERIAL           | 10/840,00    | 19                 |
|   |                                       |             | APPLICANT(S) Ferrant et al.           | <u>-</u> -       |              |                    |
|   | AN ATAM AFTIRE F                      | e a tradent | FILING DATE                           |                  |              |                    |
| INFORMATION   | ON DISCLOSURE 51<br>BY APPLICANT      | IVIEWEM     | May 6, 2004                           |                  | 2819         |                    |
|   |                                       | T.          | S. PATENT DOCUMENTS                   | <del></del>      |              |                    |
| EXAMINER<br>INITIALS  | DOCUMENT<br>NUMBER                    | DATE        | NAME                                  | CLASS            | SUB<br>CLASS | PILING<br>DATE     |
|   | · · · · · · · · · · · · · · · · · · · |             |                                       |                  |              |                    |
|   |                                       | FOR)        | EIGN PATENT DOCUMENTS                 |                  |              |                    |
| EXAMINER<br>INITIALS  | DOCUMENT<br>NUMBER                    | DATE        | COUNTRY                               | CLASS            | SUB<br>CLASS | TRAFSLATE<br>YESHO |
| Ca)   | FR 2 197 484                          | 3/1974      | French                                |                  |              |                    |
|   | EP 1 180 799                          | 2/2002      | European                              |                  |              |                    |
|   | EP 0 030 856                          | 6/1981      | European                              |                  |              |                    |
|   | GB 1 414 228                          | 11/1975     | Great Britain                         |                  |              |                    |
|   | EP 0 694 977                          | 1/1986      | European                              |                  |              |                    |
|   | EP 1 237 193                          | 9/2002      | European                              |                  |              |                    |
|   | EP 0 878 804                          | 11/1998     | European                              |                  |              |                    |
|   | EP 0 801 427                          | 10/1997     | European                              |                  |              |                    |
|   | EP 0 513 923                          | 11/1992     | European                              |                  |              |                    |
|   | EP 0 731 972                          | 11/2001     | European                              |                  |              |                    |
| ·   | EP 0 362 961                          | 2/1994      | European                              |                  |              |                    |
|   | EP 1 288 955                          | 3/2003      | European                              |                  |              |                    |
| 4)  | EP 1 280 205                          | 1/2003      | Еигореап                              |                  |              |                    |
| T   | OTHER!                                | DOCUMENTS   | Including Author, Title, Date, Pertin | ent Pages, Etc.) |              |                    |
|   |                                       |             |                                       |                  |              |                    |
| XAMINER   | SON DIN                               | ıH          | DATE CONSIDERED                       | 12/9/            | 104          |                    |



|                               |                                    | •               |   |                 | U            | Sheet 2           |
|-------------------------------|------------------------------------|-----------------|---|-----------------|--------------|-------------------|
|                               | _                                  |                 | ATTY. DOCKET NO.  | SERIALI         | VUMILER      | QUEEK A           |
|                               | PTO-1449 (Modified)                |                 | 211.004-US  |                 | 10/840,00    | )9                |
| U.S. DRF<br>PATENT            | ARTMENT OF COMM<br>AND TRADEMARK O | erce<br>Fyice   | APPLICANT(S) Ferrant et al.                                     |                 |              |                   |
|                               |                                    |                 | FILING DATE   | GROUP /         | RT UNIT      | ······            |
| INFORMAT                      | ION DISCLOSURE STA<br>BY APPLICANT | TEMENT          | May 6, 2004   |                 | 2818         |                   |
|                               |                                    | U.S.            | PATENT DOCUMENTS  |                 |              |                   |
| EXAMINER<br>INITIALS          | DOCUMENT<br>NUMBER                 | DATE            | NAME  | CLASS           | SUB<br>CLASS | PILING<br>DATE    |
|                               |                                    |                 |   |                 |              |                   |
| •                             |                                    |                 |   |                 |              |                   |
|                               |                                    | FORE            | IGN PATENT DOCUMENTS  |                 |              |                   |
| XAMINER<br>INITIALS           | DOCUMENT<br>NUMBER                 | DATE            | COUNTRY   | CLASS           | SUB<br>CLASS | TRAFFLAT<br>YERMO |
| 40                            | EP 1 253 634 A2                    | 10/2002         | European  |                 |              |                   |
|                               | EP 1 241 708 A2                    | 9/2002          | European  |                 |              |                   |
|                               | EP 1 209 747 A2                    | 5/2002          | European  |                 |              |                   |
|                               | EP 1 204 147 A1                    | 5/2002          | European  |                 |              |                   |
|                               | EP 1 204 146 A1                    | 5/2002          | European  |                 |              |                   |
|                               | EP 1 179 850 A2                    | 2/2002          | European  |                 |              |                   |
|                               | EP 1 182 744 A1                    | 12/2001         | European  |                 |              |                   |
|                               | EP 1 182 663 A2                    | 12/2001         | European  |                 |              |                   |
|                               | EP 1 073 121 A2                    | 1/2001          | European  |                 |              |                   |
|                               | EP 0 993 037 A2                    | 4/2000          | European  |                 |              |                   |
|                               | EP 0 980 101 A2                    | 2/2000          | European  |                 |              |                   |
|                               | EP 0 971 360 A1                    | 1/2000          | European  |                 |              |                   |
|                               | EP 0 951 072 A1                    | 10/1999         | European  |                 |              |                   |
| 40                            | EP 0 933 820 A1                    | 8/1999          | European  | ·               |              |                   |
|                               | OTHER DO                           | CUMENTS (       | peluding Author, Title, Date, Pertiac                           | nt Pages, Rec.) |              |                   |
|                               |                                    | · · · · · ·     |   | <del></del>     |              |                   |
|                               | <u></u>                            |                 |   |                 |              |                   |
| EXAMINER                      | SON DINH                           |                 | DATE CONSIDERED   | 12/9/0          | 4            |                   |
| EXAMINER: 1<br>considered. In |                                    | e was considere | d. Draw tine through election if not<br>untention to applicant. | <del></del>     |              | 9 and n           |

Sheet 3 of 5 ATTY. DOCKET NO. SERIAL NUMBER PTO-1449 (Modified) 10/840,009 211,004-US U.S. DEPARTMENT OF COMMERCE APPLICANT(S) PATENT AND TRADEMARK OFFICE Ferrant et al. GROUP ART UNIT FILING DATE INFORMATION DISCLOSURE STATEMENT 2813 May 6, 2004 BY APPLICANT U.S. PATENT DOCUMENTS SUB PHI.ING NAME DATE DOCUMENT **EXAMINER** CLASS DATE NUMBER INITIALS FOREIGN PATENT DOCUMENTS TRAIGLATION St B EXAMINER DOCUMENT CLASS CLASS DATE COUNTRY INTUALS NUMBER EP 0 924 766 A2 6/1999 European 41) EP 0 920 059 A2 6/1999 European EP 0 869 511 A2 10/1998 European EP 0 860 878 A2 8/1998 European 8/1998 European EP 0 858 109 A2 EP 0 844 671 B1 11/2002 European 5/2000 Européan EP 0 836 194 B1 European 8/1997 EP 0 788 165 A2 8/2002 European EP 0 744 772 81 European EP 0 739 097 A2 10/1996 EP 0 727 822 B1 8/1999 European European 8/1996 EP 0 727 820 A1 4 9/2001 European EP 0 726 601 B1 OTHER DOCUMENTS (Including Author, Tifle, Date, Pertinent Pages, Etc.) 12/9/04 DATE CONSIDERED **EXAMINER** SON DINH

considered. Include copy of this form with next communication to applicant.

EXAMINER: Initial citation if reference was considered. Draw line through citation if not in conformance to MPEP 609 and not

11/19/2004 . 10:47.



STEINBERG

|  |                           |                             | ATTY. DOCKET NO.                       | SERIAL          | UMBER        |                    |  |
|--|---------------------------|-----------------------------|--|-----------------|--------------|--------------------|--|
|  | PTO-1449 (Modified)       |                             | 211.004-US                             |                 | 10/840,00    | 09                 |  |
| U.S. DEPARTMENT OF COMMERCE<br>PATENT AND TRADEMARK OFFICE |                           | APPLICANT(5) Ferrant et al. |  |                 |              |                    |  |
| INFORMATION DISCLOSURE STATEMENT<br>BY APPLICANT           |                           | TRMENT                      | FILING DATE                            | GROUP A         | RTINIT       |                    |  |
|  |                           | May 6, 2004                 |  | 281:3           |              |                    |  |
|  | ·                         | v.s                         | PATENT DOCUMENTS                       |                 |              | 1                  |  |
| EXAMINER<br>INITIALS                                       | DOCUMENT<br>NUMBER        | DATE                        | NAME                                   | CLASS           | SUB<br>CLASS | FILING<br>DATE     |  |
| IIII LIKLIS  | 110,000                   |                             |  |                 |              |                    |  |
|  |                           |                             |  |                 |              |                    |  |
| ·  | <u> </u>                  | FORE                        | ign patent documents                   |                 |              |                    |  |
| XAMINER  | DOCUMENT                  |                             | COLDANA                                | CLASS           | SUB<br>CLASS | TRANSLATI<br>VENNO |  |
| CA)  | NUMBER<br>EP 0 725 402 B1 | 9/2002                      | COUNTRY                                | CLASS           | CLASS        |                    |  |
| 1  | EP 0 689 252 B1           | 8/2000                      | European                               |                 |              |                    |  |
|  | EP 0 682 370 B1           | 9/2000                      | European                               |                 |              |                    |  |
|  | EP 0 642 173 B1           | 7/1999                      | European                               |                 |              |                    |  |
|  | EP 0 608 758 B1           | 9/2000                      | European                               |                 |              |                    |  |
|  | EP 0 601 590 B1           | 4/2000                      | European                               |                 |              |                    |  |
|  | EP 0 599 506 A1           | 6/1994                      | European                               |                 |              |                    |  |
|  | EP 0 599 388 B1           | 8/2000                      | European                               |                 |              |                    |  |
|  | EP 0 579 566 A2           | 1/1994                      | European                               |                 |              |                    |  |
|  | EP 0 564 204 A2           | 10/1993                     | European                               |                 |              |                    |  |
|  | EP 0 537 677 B1           | 8/1998                      | European                               |                 |              |                    |  |
|  | EP 0 510 607 B1           | 2/1998                      | European                               |                 |              |                    |  |
| 47   | EP 0 465 961 B1           | 8/1995                      | European                               |                 |              |                    |  |
|  | OTHER D                   | OCUMENTS (I                 | neluding Author, Title, Date, Pertiner | nt Pages, Etc.) |              |                    |  |
|  |                           | · <del></del>               |  |                 |              |                    |  |
| i  |                           | ·                           |  |                 |              |                    |  |
| XAMINER  | SON DINT                  | -                           | DATE CONSIDERED                        | 12/9/0          | 4            |                    |  |

COPY

|                      |  |             | _                                   |                   | U             | Sheet 5 of               |  |
|----------------------|--|-------------|-------------------------------------|-------------------|---------------|--------------------------|--|
|                      |  |             | ATTY. DOCKET NO.                    | SERIALN           | UMHER         |                          |  |
|                      | PTO-1449 (Modified)  |             | 211.004-US                          |                   | 10/840,00     | 19                       |  |
|                      | ARTMENT OF COMMI   |             | APPLICANT(S)                        |                   |               |                          |  |
| Mina                 | <b>74.12</b> , <b>4.12</b> |             | Ferrant et al.                      | GROUP ART UNIT    |               |                          |  |
| INFORMATI            | TION DISCLOSURE STATEMENT  NAME OF A PRINCIPLE OF A   |             | 1                                   | 281B              |               |                          |  |
|                      | BY APPLICANT   |             |                                     |                   |               |                          |  |
|                      |  | <u> </u>    | PATENT DOCUMENTS                    |                   |               |                          |  |
| EXAMINER<br>INITIALS | DOCUMENT<br>NUMBER   | DATE        | NAMB                                | CLASS             | SUB<br>CLASS  | PILING<br>DATE           |  |
| HALLIALS             | .,,,,,,,,,   |             |                                     |                   |               |                          |  |
|                      | -  |             |                                     |                   | ļ <del></del> |                          |  |
|                      |  |             |                                     |                   | <b>L</b>      | L                        |  |
|                      |  | PORE        | IGN PATENT DOCUMENTS                |                   | <del></del>   |                          |  |
| PXAMINER             | DOCUMENT<br>NUMBER   | DATE        | COUNTRY                             | CLASS             | St B<br>CLASS | HENTA, KENJART<br>GIORRY |  |
| initials<br>(h)      | EP 0 366 882 B1  | 5/1995      | European                            |                   |               |                          |  |
| <del>- (~</del>      | EP 0 359 551 B1  | 12/1994     | European                            |                   |               |                          |  |
|                      |  |             |                                     |                   |               |                          |  |
|                      | EP 0 354 348 A2  | 2/1990      | European                            |                   |               |                          |  |
|                      | EP 0 350 057 B1  | 1/1990      | European                            |                   |               |                          |  |
|                      | EP 0 333 426 B1  | 7/1996      | European                            |                   |               |                          |  |
|                      | EP 0 300 157 B1  | 5/1993      | European                            |                   |               |                          |  |
|                      | EP 0 253 631 B1  | 4/1992      | European                            |                   |               |                          |  |
|                      | EP 0 245 515 B1  | 4/1997      | European                            |                   |               |                          |  |
|                      | EP 0 207 619 B1  | 8/1991      | European                            |                   |               |                          |  |
|                      | EP 0 202 515 B1  | 3/1991      | European                            |                   |               |                          |  |
|                      | EP 0 175 378 B1  | 11/1991     | European                            |                   |               |                          |  |
|                      | EP 1 191 596 A2  | 3/2002      | European                            |                   |               |                          |  |
| 40                   | EP 1 233 454 A2  | 8/2002      | European                            |                   |               |                          |  |
|                      | OTHER DO   | CUMENTS (I  | ncluding Author, Title, Date, Perti | nent Pages, Etc.) |               | <u>.</u>                 |  |
|                      |  | <del></del> |                                     | -                 |               |                          |  |
|                      |  |             |                                     |                   |               |                          |  |
| EXAMINER             | SON DINI   | †           | DATE CONSIDERED                     | 12/9/             | 04            |                          |  |

considered. Include copy of this form with next communication to applicant.